NSN 5961-00-554-8212

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View Online at https://aerobasegroup.com/nsn/5961-00-554-8212

Inclosure Material:

Metal

Overall Length:

0.210 inches

Terminal Length:

0.500 inches

Overall Diameter:

0.230 inches

Internal Configuration:

Junction contact

Mounting Method:

Terminal

Terminal Circle Diameter:

0.100 inches

Features Provided:

Hermetically sealed case

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

10.0 collector to emitter voltage/static/base open and 20.0 collector to base voltage, dc and 3.0 emitter to base voltage, dc

Current Rating Per Characteristic:

100.00 milliamperes source cutoff current

Power Rating Per Characteristic:

350.0 milliwatts small-signal input power, common-collector absolute

Transfer Ratio:

10.0 static forward current transfer ratio, common-emitter

Maximum Operating Tempurature Per Measurement Point:

200.0 degrees celsius junction

Special Features:

Junction pattern arrangement: npn

Precious Material And Location:

Lead surfaces gold

Precious Material:

Gold

Terminal Type And Quantity:

4 uninsulated wire lead

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

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